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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	10/799318
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	
Examiner Name	Unassigned
Attorney Docket Number	200315719-1

Sheet 2 of 2

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MLP		Proceedings of the IEEE, Proceedings Letters, November 1968, pgs 2094-2095.	
MLP		Extended abstracts of the 2000 International Conference on Solid State Devices and Materials; Aug 29-31, 2000, Sendai Intl Center, pgs 128-129.	
MLP		OHTOMO, "Novel Semiconductor Technologies of ZnO Films towards...", IEICE Trans. Electron., Vol E83-C, No 10, Oct 2000, pgs 1614-1617.	

Examiner Signature	<i>Mark D. [Signature]</i>	Date Considered	3/19/2007
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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#2 IDS
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FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

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REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
MP	1A	4,887,255	12/12/1989	Handa, et al.	
	1B	5,744,864	04/28/1998	Cillelsen, et al.	
	1C	6,225,655	05/01/2001	Moise, et al.	
	1D	6,255,130	07/03/2001	Kim	
	1E	6,362,499	03/26/2002	Moise, et al.	
	1F	6,563,174	05/13/2003	Kawasaki, et al.	
	1G	2003/0013261	01/16/2003	Asano	
	1H	2002/0153587	10/24/2002	Adkisson, et al.	
	1I	2003/0207502	11/06/2003	Yamazaki, et al.	
	1J	2003/0218221	11/27/2003	Wager, III, et al.	
MP	1K	2003/0218222	11/27/2003	Wager, III, et al.	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
MP	1L	WO 97/06544	02/20/1997	Cillelsen, et al.		
MP	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
MP	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
MP	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

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MP	2A	2003/0219530	11/27/2003	Yamazaki, et al.	
	2B	2003/0111663	06/19/2003	Yagi	
	2C	2003/0047785	03/13/2003	Kawasaki, et al.	
	2D	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
	2E	10/763,353	01/23/2004		Semiconductor Device
MP	2F	10/763,354	01/23/2004		Transistor including a Deposited Channel Region Having a ...
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527.
MP	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
MP	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
MP	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
MP	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
MP	4R	Pallecchi, Ilaria, et al. "SrTiO3-based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
MP	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

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NSP	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
NSP	5R	Uneno, K., et al. "Field-effect transistor on SrTiO3 with sputtered Al2O3 gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
NSP	5S	Wöllensteien, Jürgen, et al., "An insulated gate thin-film transistor using SnO2 as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

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MP	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO ₃ Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
MP	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
MP	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).

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